2SC3332

ON Semiconductor®

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Bipolar Transistor 160V, 0.7A, Low VCE(sat) NPN Single NP

Features

- · Hgih breakdown voltage
- · Excellent hFE linearity
- · Wide SOA and highly resistant to breakdown
- · Adoption of MBIT process

Specifications

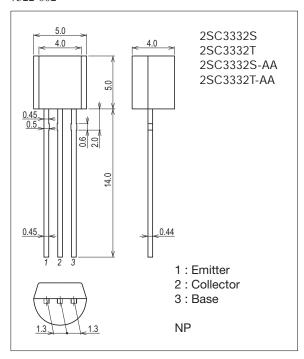
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector to Base Voltage	VCBO		180	V
Collector to Emitter Voltage	VCEO		160	V
Emitter to Base Voltage	VEBO		6	V
Collector Current	IC		0.7	А
Collector Current (Pulse)	ICP		1.5	А
Collector Dissipation	PC		700	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7522-002



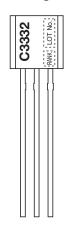
Product & Package Information

• Package : NP

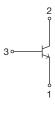
• JEITA, JEDEC : SC-34A, TO-92, TO-226AA, SOT-54

• Minimum Packing Quantity: 1,500 pcs./box, 500pcs./bag

Marking



Electrical Connection



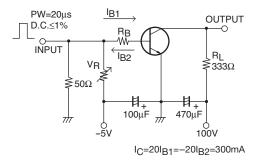
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter	Syllibol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =120V, I _E =0A			0.1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0A			0.1	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =5V, I _C =100mA	140*		400*	
	h _{FE} 2	V _{CE} =5V, I _C =10mA	80			
Gain-Bandwidth Product	fŢ	V _{CE} =10V, I _C =50mA		120		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		8		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	I _C =250mA, I _B =25mA		0.12	0.4	V
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C =250mA, I _B =25mA		0.85	1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A				V
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	160			V
Emitter to Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	6			V
Turn-ON Time	ton			50		ns
Storage Time	t _{stg}	See specified Test Circuit.		1000		ns
Fall Time	tf			60		ns

*: The 2SC3332 is classified by 100mA hFE as follows:

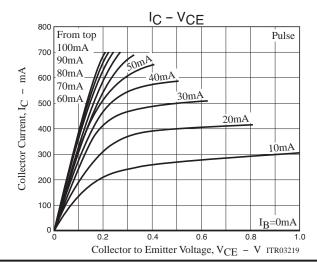
Rank	S	T
hFE	140 to 280	200 to 400

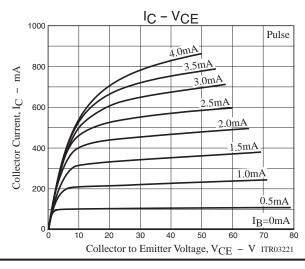
Switching Time Test Circuit

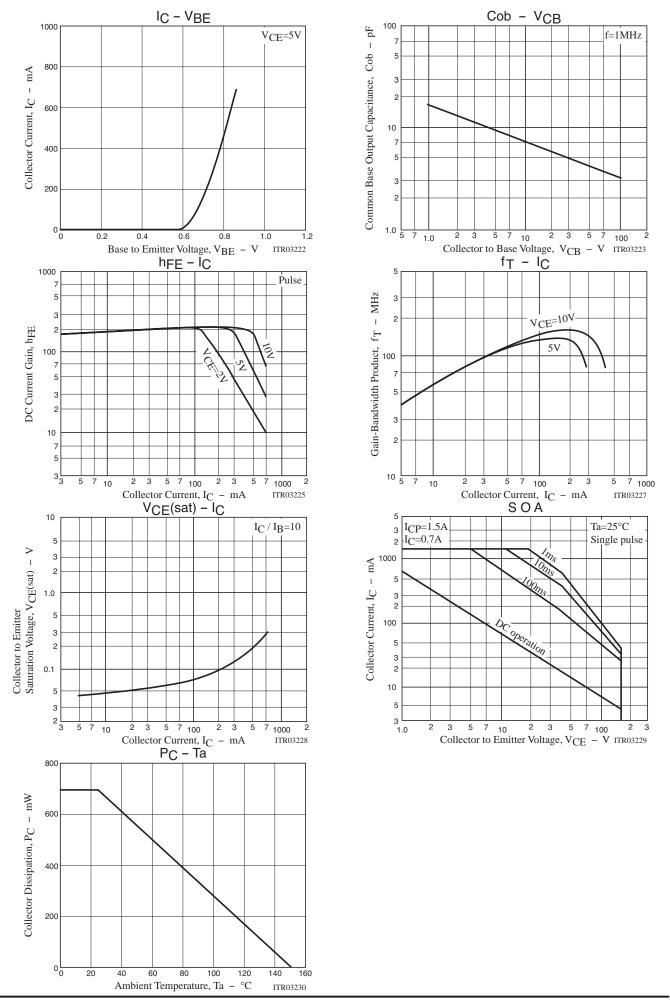


Ordering Information

Device	Package	Shipping	memo	
2SC3332S	NP	500pcs./bag		
2SC3332T	NP	500pcs./bag	Pb Free	
2SC3332S-AA	NP	1,500pcs./box	Pb Flee	
2SC3332T-AA	NP	1,500pcs./box		

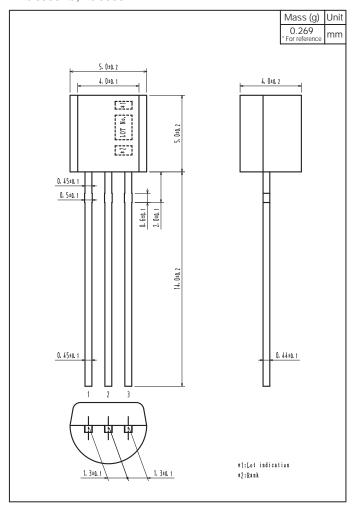






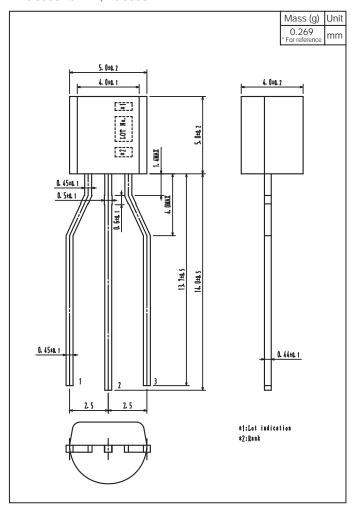
Outline Drawing

2SC3332S, 2SC3332T



Outline Drawing

2SC3332S-AA, 2SC3332T-AA



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